
HL7851G

GaAlAs Laser Diode

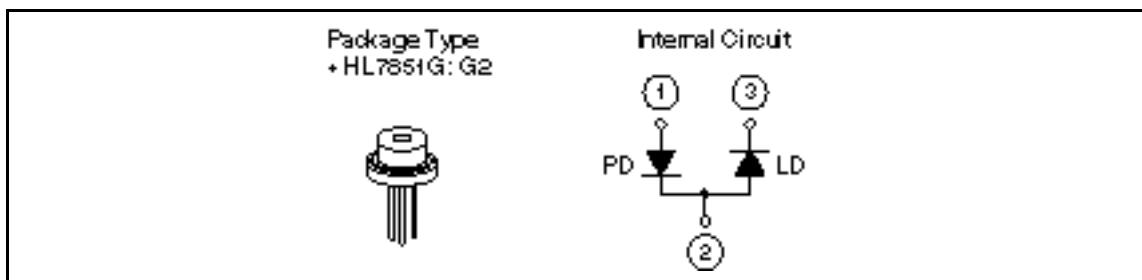
HITACHI

Description

The HL7851G is a high power 0.78 μm band GaAlAs laser diode with a multi-quantum well (MQW) structure. It is suitable as a light source for optical disk memories, levelers and various other types of optical equipment. Hermetic sealing of the package assures high reliability.

Features

- Σ Visible light output: $\lambda_p = 785 \text{ nm}$ Typ
- Σ Small beam ellipticity: 9.5:23
- Σ High output power: 50 mW (CW)
- Σ Built-in monitor photodiode



HL7851G

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

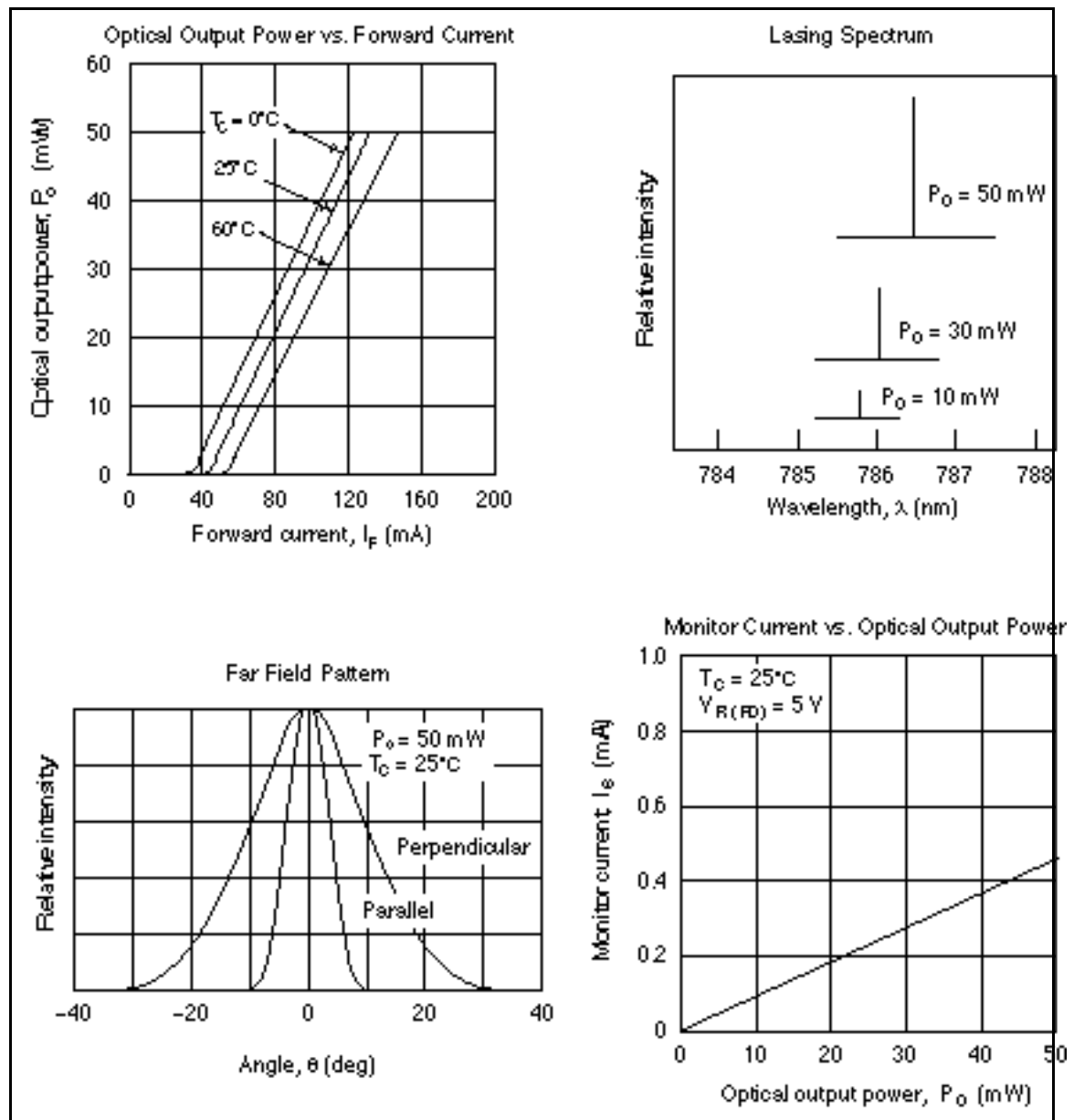
Item	Symbol	Rated Value	Unit
Optical output power	P_O	50	mW
Pulse optical output power	$P_{O(\text{pulse})}$	60 ^{*1}	mW
LD reverse voltage	$V_{R(\text{LD})}$	2	V
PD reverse voltage	$V_{R(\text{PD})}$	30	V
Operating temperature	T_{opr}	-10 to +60	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +85	$^\circ\text{C}$

Note: 1. Maximum 50% duty cycle, maximum 1 μs pulse width

Optical and Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Optical output power	P_O	50	—	—	mW	Kink free
Threshold current	I_{th}	—	45	70	mA	
Slope efficiency	h	0.35	0.55	0.7	mW/mA	40 mW/ $I_{(45\text{ mW})} - I_{(5\text{ mW})}$
Operating current	I_{op}	—	140	170	mA	$P_O = 50\text{ mW}$
LD Operating voltage	V_{op}	—	2.3	2.7	V	$P_O = 50\text{ mW}$
Lasing wavelength	λ_p	775	785	795	nm	$P_O = 50\text{ mW}$
Beam divergence (parallel)	$q_{//}$	8	9.5	12	deg.	$P_O = 50\text{ mW}$, FWHM
Beam divergence (perpendicular)	$q^\perp$	18	23	28	deg.	$P_O = 50\text{ mW}$, FWHM
Monitor current	I_s	25	—	150	μA	$P_O = 5\text{ mW}$, $V_{R(\text{PD})} = 5\text{ V}$
Astigmatism	A_s	—	5	—	μm	$P_O = 5\text{ mW}$, NA = 0.4

Typical Characteristic Curves



Typical Characteristic Curves (cont)

